L Number	Hits	Search Text	DB	Time stamp
-	1	10/665412	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 13:24
-	46291	(resist or photoresist or photopolymer) with (Si! or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 13:25
-	93664	(resist or photoresist or $6lithogr$6) and (re$work or rework or strip or stripped ir stripping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 13:44
-	10244	((resist or photoresist or photopolymer) with (Si! or silicon)) and ((resist or photoresist or $6lithogr$6) and (re$work or rework or strip or stripped ir stripping))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 13:28
-	1133	(((resist or photoresist or photopolymer) with (Si! or silicon)) and ((resist or photoresist or $6lithogr$6) and (re$work or rework or strip or stripped ir stripping))) and (solvent same (THF or PGMEA or DMSO or ketones or esters or lactates))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:57
-	85	((((resist or photoresist or photopolymer) with (Si! or silicon)) and ((resist or photoresist or $6lithogr$6) and (re$work or rework or strip or stripped ir stripping))) and (solvent same (THF or PGMEA or DMSO or ketones or esters or lactates))) and ((re$coat or coat) same (re$expos$4 or expos$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 13:31
-	80443	(resist or photoresist or $6lithogr$6) and (strip or stripped or stripping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:19
-	619	((resist or photoresist or $6lithogr$6) and (strip or stripped or stripping)) and (re$work or rework)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 13:46
-	39	(((resist or photoresist or $6lithogr$6) and (strip or stripped or stripping)) and (re$work or rework)) and ((solvent or solution) same (THF or PGMEA or DMSO or ketones or esters or lactates))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 16:40

-	1400	430/329	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:10
-	1	430/329 and (chemical$3 near amplif$9) with (si or sily$9 or silane or $9sesquioxane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:15
-	1	430/329 and ((chemical$3 near amplif$9) with (si or silo$9 or silane or $9sesquioxane))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:16
-	8	430/329 and ((chemical$3 near amplif$9) with (Si or silicon or (silicon near (bearining or containing))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:53
-	553	430/329 and (resist or photoresist or $6lithogr$6) and (strip or stripped or stripping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:47
-	27	(430/329 and (resist or photoresist or $6lithogr$6) and (strip or stripped or stripping)) and (chemical$3 near2 amplif$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:49
-	1127	430/329 and (resist or photoresist or $6lithogr$6) and (strip or stripped or stripping or stripper or remov$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:38
-	68	(430/329 and (resist or photoresist or $6lithogr$6) and (strip or stripped or stripping or stripper or remov$4)) and (chemical$3 near2 amplif$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:39
-	41	((430/329 and (resist or photoresist or $6lithogr$6) and (strip or stripped or stripping or stripper or remov$4)) and (chemical$3 near2 amplif$8)) not ((430/329 and (resist or photoresist or $6lithogr$6) and (strip or stripped or stripping)) and (chemical$3 near2 amplif$8))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:44
-	4690	(438/689,694).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:44

-	467	((438/689,694).CCLS.) and (resist or photoresist or $6lithogr$6) and (strip$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:53
-	14	(((438/689,694).CCLS.) and (resist or photoresist or $6lithogr$6) and (strip$5)) and (chemical$3 near2 amplif$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:52
-	3810	(134/1,1.3,26).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:53
-	365	((134/1,1.3,26).CCLS.) and (resist or photoresist or $6lithogr$6) and (strip$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 16:38
-	0	(((134/1,1.3,26).CCLS.) and (resist or photoresist or $6lithogr$6) and (strip$5)) and ((chemical$3 near amplif$9) with (Si or silicon or (silicon near (bearining or containing))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:54
-	396	(resist or photoresist or photopolymer) with ((chemical$3 near amplif$9) with (Si or $6sesquioxane or silane or $6siloxane or silicon or (silicon near (bearining or containing))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 16:36
-	0	(((134/1,1.3,26).CCLS.) and (resist or photoresist or $6lithogr$6) and (strip$5)) and ((resist or photoresist or photopolymer) with ((chemical$3 near amplif$9) with (Si or $6sesquioxane or silane or $6siloxane or silicon or (silicon near (bearining or containing)))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 15:56
-	62	(((134/1,1.3,26).CCLS.) and (resist or photoresist or $6lithogr$6) and (strip$5)) and (solvent same (THF or PGMEA or DMSO or ketones or esters or lactates))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 16:23
-	742	(resist or photoresist or photopolymer or (photo near sensitive)) and ((chemical$3 near amplif$9) same (Si or $6sesquioxane or silane or $6siloxane or silicon or (silicon near (bearining or containing))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 17:28
-	22653	(resist or photoresist or photopolymer or (photo near sensitive)) near6 strip$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 17:18

-	364640	((solvent or solution or strip$5) same (THF or PGMEA or pgme or DMSO or ketone or esters or lactate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 16:41
-	28	((resist or photoresist or photopolymer or (photo near sensitive)) and ((chemical$3 near amplif$9) same (Si or $6sesquioxane or silane or $6siloxane or silicon or (silicon near (bearining or containing))))) and ((resist or photoresist or photopolymer or (photo near sensitive)) near6 strip$5) and (((solvent or solution or strip$5) same (THF or PGMEA or pgme or DMSO or ketone or esters or lactate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 16:42
-	22	hardened near photoresist	IBM_TDB	2004/07/30 17:17
-	0	((resist or photoresist or photopolymer or (photo near sensitive)) and ((chemical$3 near amplif$9) same (Si or $6sesquioxane or silane or $6siloxane or silicon or (silicon near (bearining or containing))))) and (((solvent or solution or strip$5) same (THF or PGMEA or pgme or DMSO or ketone or esters or lactate)))	IBM_TDB	2004/07/30 17:17
-	445	(resist or photoresist or photopolymer or (photo near sensitive)) near6 (wet near strip$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 17:19
-	3	((resist or photoresist or photopolymer or (photo near sensitive)) and ((chemical$3 near amplif$9) same (Si or $6sesquioxane or silane or $6siloxane or silicon or (silicon near (bearining or containing))))) and ((resist or photoresist or photopolymer or (photo near sensitive)) near6 (wet near strip$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 17:20
-	40	(((solvent or solution or strip$5) same (THF or PGMEA or pgme or DMSO or ketone or esters or lactate))) and ((resist or photoresist or photopolymer or (photo near sensitive)) near6 (wet near strip$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/30 17:23